



503.37698X00
Response Under 37 CFR 1.116
Expedited Procedure
Group No. 1763

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): TAKAHASHI, et al.

Serial No.: 09/414,520

Filed: October 8, 1999

For: PLASMA PROCESSING APPARATUS AND A PLASMA
PROCESSING METHOD

Group: 1763

Examiner: Zervigon, R.

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AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

December 3, 2001

Sir:

In response to the Office Action of August 3, 2001,
please amend the application as follows:

IN THE CLAIMS

Please amend Claims 1, 2, 6 and 7 as follows:

1. (three times amended) In a plasma processing apparatus
for etching an insulating film, the plasma processing
apparatus having a vacuum processing chamber, a sample
table for mounting a sample which is processed in said
vacuum processing chamber, and a plasma generation means,
wherein a plasma processing is carried out by generating a
plasma in response to introduction of a gas which contains
at least carbon and fluorine, and a gas species is